



TO-126

2P4M Silicon Controlled Rectifier

MAIN FEATURES

Symbol	value	unit
$I_{T(RMS)}$	2	A
V_{DRM}/V_{RRM}	2P4M-6	400
	2P4M-8	600
T_j	Junction Temperature	-40 ~ 125 °C
T_{stg}	Storage Temperature	-55 ~ 150 °C

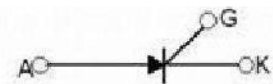
1.KATHODE

2.GATE

3.ANODE



1 2 3



DESCRIPTION

Logic level sensitive gate triac intended to be interfaced directly to microcontrollers, logic integrated circuits and other low power gate trigger circuits.

FEATURES

- Blocking voltage to 400 V
- RMS on-state current to 2A
- General purpose switching

APPLICATIONS

- General purpose switching
- Phase control applications
- Solid state relays

ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Max	Unit	
On state voltage *	V_{TM}	$I_{TM}=1A$		1.7	V	
Gate trigger voltage	V_{GT}	$V_{AK}=7V$		0.8	V	
Peak Repetitive forward and reverse blocking voltage	V_{DRM}/V_{RRM}	$I_{DRM}/I_{RRM}= 10 \mu A$	400 600		V	
Peak forward or reverse blocking Current	I_{DRM} I_{RRM}	$V_{AK} = \text{Rated}$ V_{DRM} or V_{RRM}		10	μA	
Holding current	I_H	$I_{HL}=20mA, V_{AK} = 7V$		5	mA	
Gate trigger current	I_{GT}	$V_{AK}=7V$	A2	5	15	μA
			A1	15	30	μA
			A	30	80	μA
			B	80	200	μA

* Forward current applied for 1 ms maximum duration, duty cycle \leq 1%.

